2SA1283

Rev.E Mar.-2016

DATA SHEET

/ Descriptions

WR0<50P ṂṂ Ŀ SQS ᴁṀ ɥ s Ⅱ ᒣ Silicon PNP transistor in a TO-92LM Plastic Package.

/ Features

[illegible] I_C [illegible] Y_{CBO}

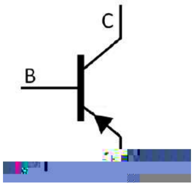
High Collector current, high Collector-base voltage.

/ Applications

[illegible]

General purpose amplifier.

/ Equivalent Circuit



/ Pinning

PIN1 χ Base PIN 2 χ Collector PIN 3 χ Emitter

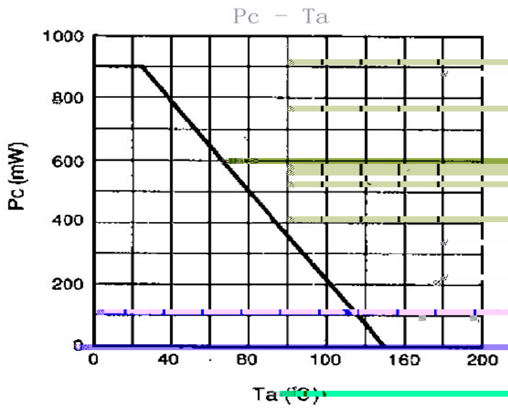
/ h_{FE} Classifications & Marking

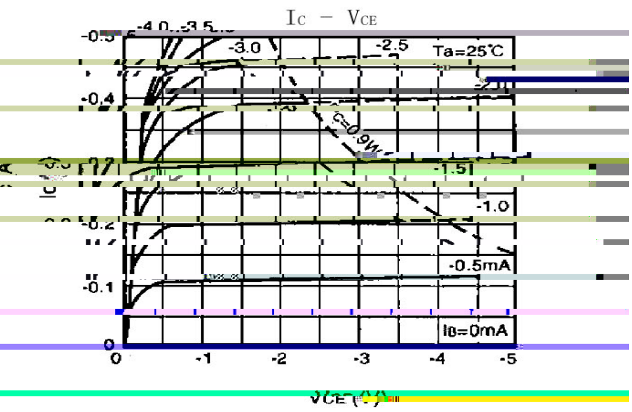
h_{FE} Classifications Symbol	C	D	E
h_{FE} Range	60~120	90~180	150~300

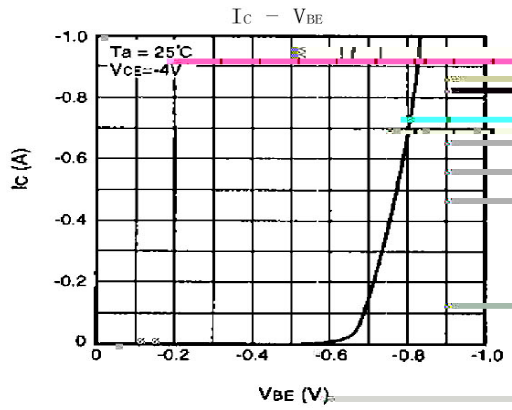
v ῼ Parameter	ɣ ᴺ Symbol	ῼӨ Rating	ᴅ ɉ Unit
Collector to Base Voltage	V_{CBO}	-60	V
Collector to Emitter Voltage	V_{CEO}	-60	V
Emitter to Base Voltage	V_{EBO}	-6.0	V
Collector Current - Continuous	I_C	-1.0	A
Collector Power Dissipation	P_C	0.9	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

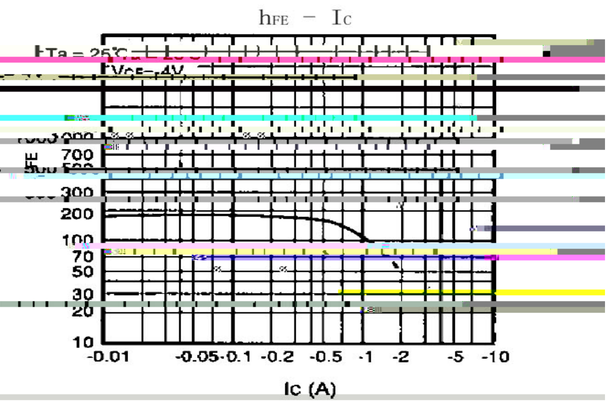
v ῼ Parameter	ɣ ᴺ Symbol	╜ ׳ ꞁ ʈ Test Conditions	ῳ ṇ Ӫ Min	Ɛ ʒ Ӫ Typ	ῳ ᶻ Ӫ Max	ᴅ ɉ Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C				

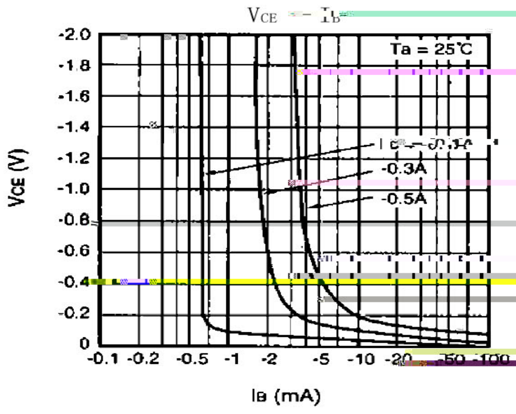
/ Electrical Characteristic Curve

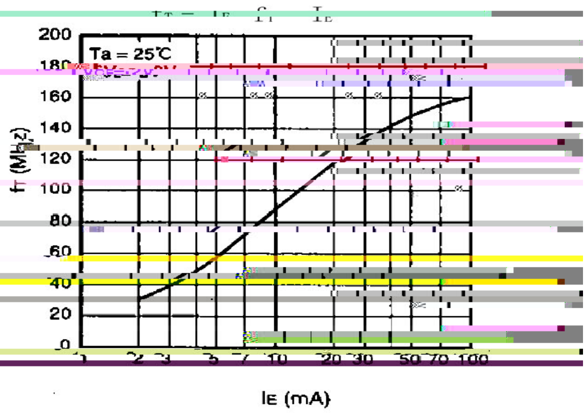

P_C − Ta


I_C − V_{CE}


I_C − V_{BE}

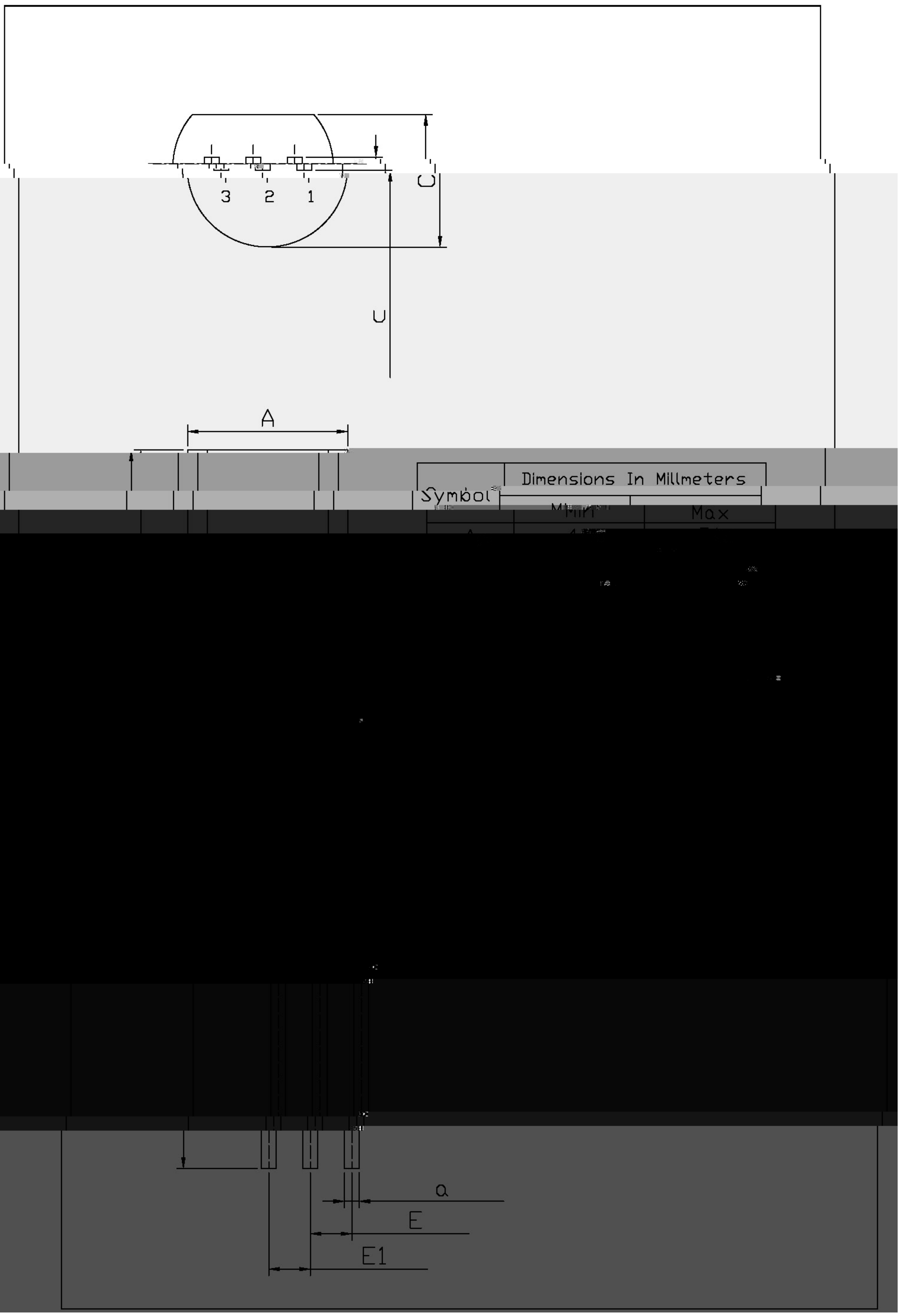

h_{FE} − I_C


V_{CE} − I_B

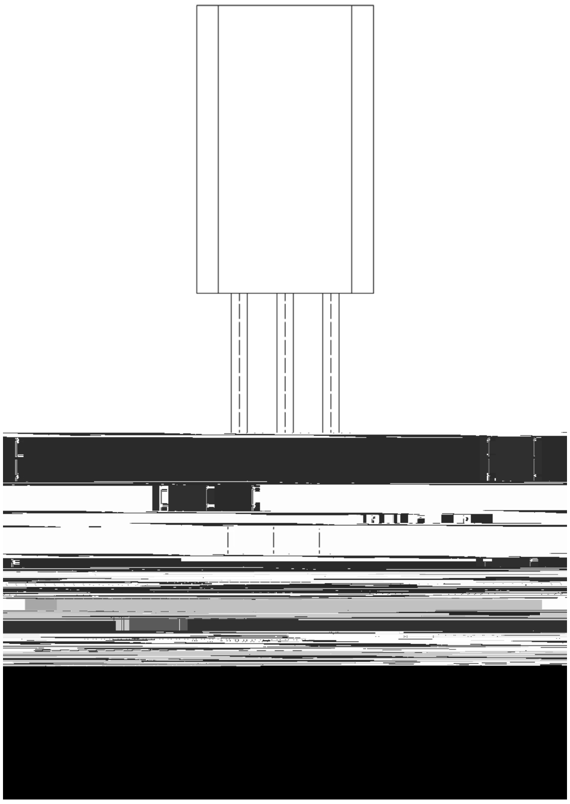

f_T − I_E

/ Package Dimensions

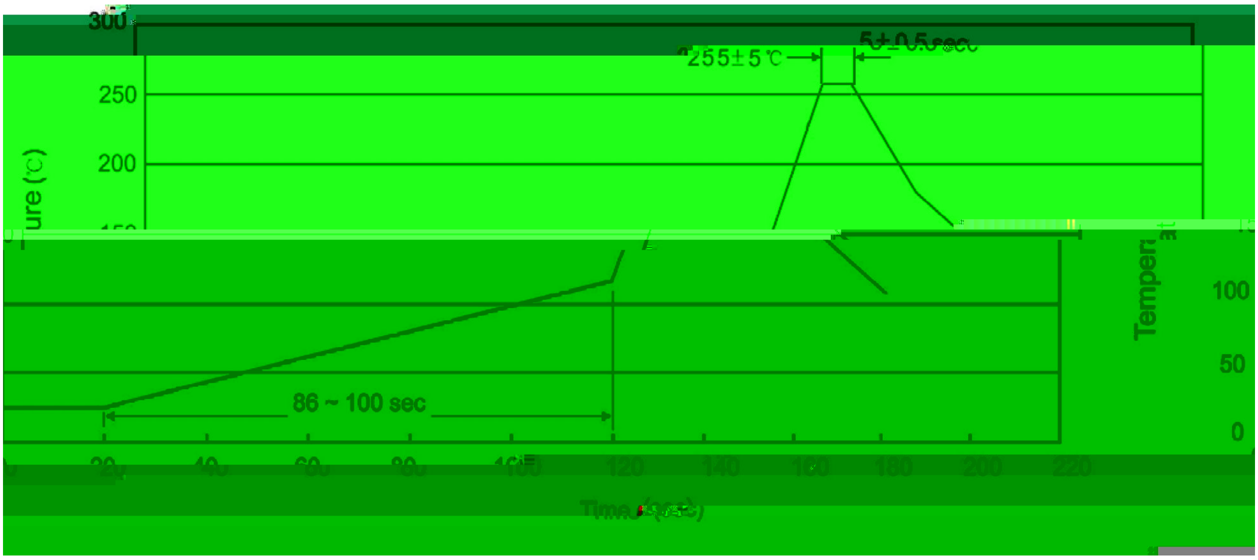
TO-92LM Unit: mm



Symbol	Dimensions In Millmeters	
	Min	Max
A	4.[illegible]	[illegible]



( ) / Temperature Profile for Dip Soldering(Pb-Free)



ب ˝ χ	Note:
1 ỉ ♬ □ ẙ 25 Ḱ 150 ɫ ı `H ڗ 60 Ḱ 90sec;	1.Preheating:25~150 ɫ , Time:60~90sec.
2 Š Ö □ ẙ 255 ° 5 ɫ ı `H ڗ 'Y ﾑ ᵯ 5 ° 0.5sec;	2.Peak Temp.:255 ° 5 ɫ , Duration:5 ° 0.5sec.
3 ì ˙ ˥ ˛ ɔ ɷ ẙ ᵯ 2 Ḱ 10 ɫ /sec.	3. Cooling Speed: 2~10 ɫ /sec.

/ Resistance to Soldering Heat Test Conditions

□ ẙ χ 270 ° 5 ɫ `H ڗ χ 10 ° ɫ sec. Tf0.56D935.8(5(.7150)]TJ/TT7 1 Tf314.9486 0